

# **isc** Silicon NPN Power Transistors

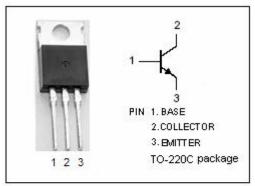
# D44C1

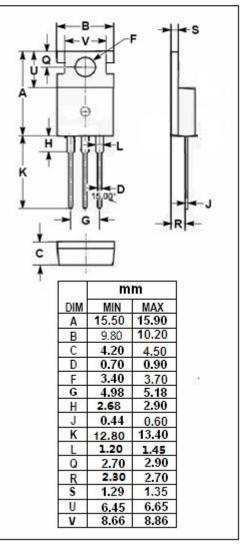
### DESCRIPTION

- Low Saturation Voltage
- Good Linearity of h<sub>FE</sub>
- Fast Switching Speeds
- Complement to Type D45C1
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

• Designed for various specific and general purpose application such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1.0MHz series, shunt and switching regulators; low and high frequency inverters/ converters and many others.





## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CES</sub>	Collector-Emitter Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ι <sub>C</sub>	Collector Current-Continuous	4	A
I <sub>CM</sub>	Collector Current-Peak	6	A
IB	Base Current-Continuous	1	А
Pc	Collector Power Dissipation @Tc=25°C	30	W
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	4.2	°C/W

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## **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 100mA			0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 100mA			1.3	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 40V, V <sub>BE</sub> = 0			10	μA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 1V	25			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 1V	10			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 20mA;V <sub>CE</sub> = 4V;f <sub>test</sub> = 1MHz		50		MHz

Switching Times

tr	Rise Time			0.3	μ <b>S</b>
ts	Storage Time	$I_{C}$ = 1A; $I_{B1}$ = - $I_{B2}$ = 0.1A; V <sub>CC</sub> = 20V		0.7	μs
tf	Fall Time			0.4	μ <b>S</b>

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